

# Silicon Carbide Schottky Diode

650 V, 30 A

## FFSH3065ADN-F155

### Description

Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

### Features

- Max Junction Temperature 175°C
- Avalanche Rated 81 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb-Free, Halogen Free/BFR Free and RoHS Compliant

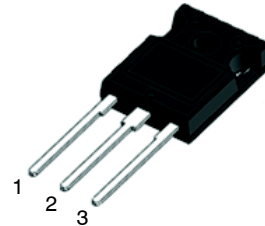
### Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

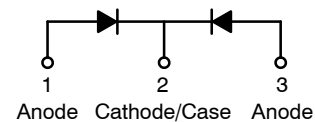


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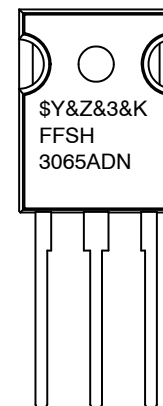
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TO-247  
LONG LEAD  
CASE 340CH



### MARKING DIAGRAM



\$Y = ON Semiconductor Logo  
&Z = Assembly Plant Code  
&3 = Numeric Date Code  
&K = Lot Code  
FFSH3065ADN = Specific Device Code

### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

# FFSH3065ADN-F155

**Table 1. ABSOLUTE MAXIMUM RATINGS** ( $T_C = 25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	FFSH3065ADN-F155	Unit
$V_{RRM}$	Peak Repetitive Reverse Voltage	650	V
$E_{AS}$	Single Pulse Avalanche Energy (Note 1)	81	mJ
$I_F$	Continuous Rectified Forward Current @ $T_C < 114^\circ\text{C}$	16*/30**	A
	Continuous Rectified Forward Current @ $T_C < 135^\circ\text{C}$	23**/36**	
$I_{F,Max}$	Non-Repetitive Peak Forward Surge Current	$T_C = 25^\circ\text{C}$ , 10 $\mu\text{s}$	1000
		$T_C = 150^\circ\text{C}$ , 10 $\mu\text{s}$	900
$I_{F,SM}$	Non-Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3$ ms	90
$I_{F,RM}$	Repetitive Forward Surge Current	Half-Sine Pulse, $t_p = 8.3$ ms	50
$P_{tot}$	Power Dissipation	$T_C = 25^\circ\text{C}$	165
		$T_C = 150^\circ\text{C}$	28
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +175	$^\circ\text{C}$
	TO247 Mounting Torque, M3 Screw	60	Ncm

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1.  $E_{AS}$  of 81 mJ is based on starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.5$  mH,  $I_{AS} = 18$  A,  $V = 50$  V.

**Table 2. THERMAL CHARACTERISTICS**

Symbol	Parameter	Rating	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.91*/0.4**	$^\circ\text{C}/\text{W}$

\* Per Leg

\*\* Per Device

**Table 3. OPERATING CHARACTERISTICS** ( $T_C = 25^\circ\text{C}$ , unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
$V_F$	Forward Voltage	$I_F = 16$ A, $T_C = 25^\circ\text{C}$	-	1.5	1.75	V
		$I_F = 16$ A, $T_C = 125^\circ\text{C}$	-	1.6	2.0	
		$I_F = 16$ A, $T_C = 175^\circ\text{C}$	-	1.72	2.4	
$I_R$	Reverse Current	$V_R = 650$ V, $T_C = 25^\circ\text{C}$	-	-	200	$\mu\text{A}$
		$V_R = 650$ V, $T_C = 125^\circ\text{C}$	-	-	400	
		$V_R = 650$ V, $T_C = 175^\circ\text{C}$	-	-	600	
$Q_C$	Total Capacitive Charge	$V = 400$ V	-	52	-	nC
C	Total Capacitance	$V_R = 1$ V, $f = 100$ kHz	-	887	-	pF
		$V_R = 200$ V, $f = 100$ kHz	-	95	-	
		$V_R = 400$ V, $f = 100$ kHz	-	72	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

## PART MARKING AND ORDERING INFORMATION

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FFSH3065ADN-F155	FFSH3065ADN	TO-247 Long Lead	Tube	N/A	N/A	30 units

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

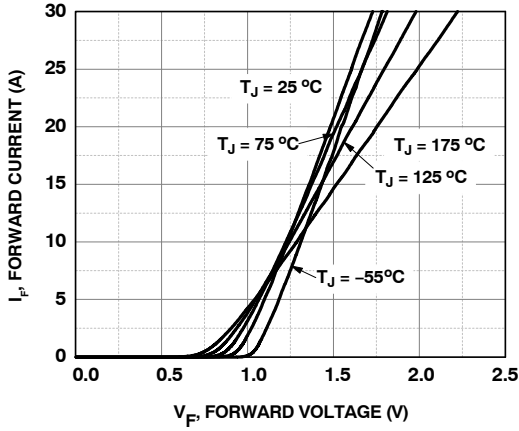


Figure 1. Forward Characteristics

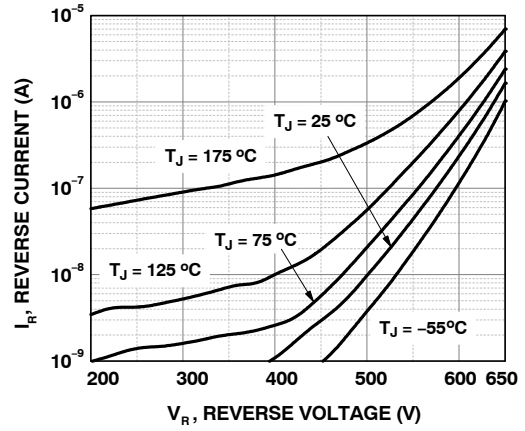


Figure 2. Reverse Characteristics

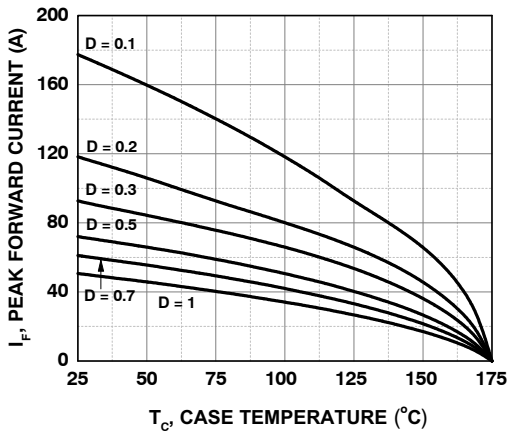


Figure 3. Current Derating

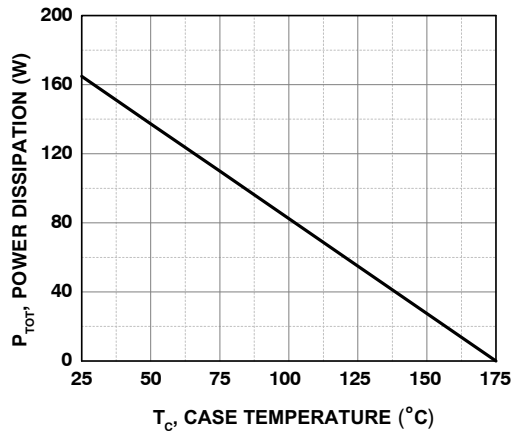


Figure 4. Power Derating

TYPICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$  unless otherwise noted)

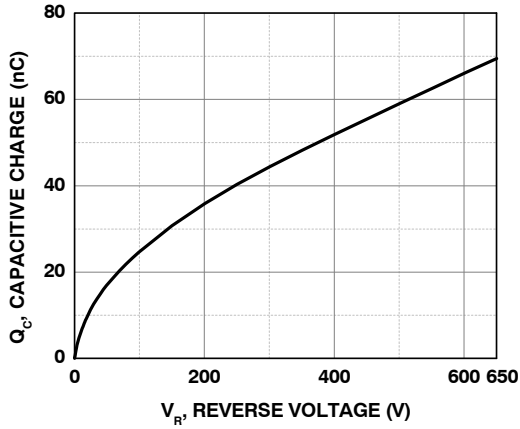


Figure 5. Capacitive Charge vs. Reverse Voltage

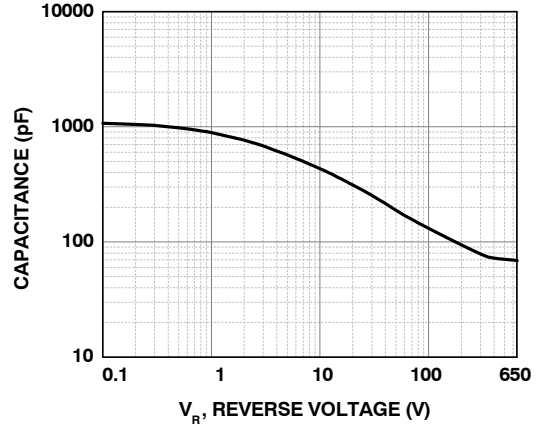


Figure 6. Capacitance vs. Reverse Voltage

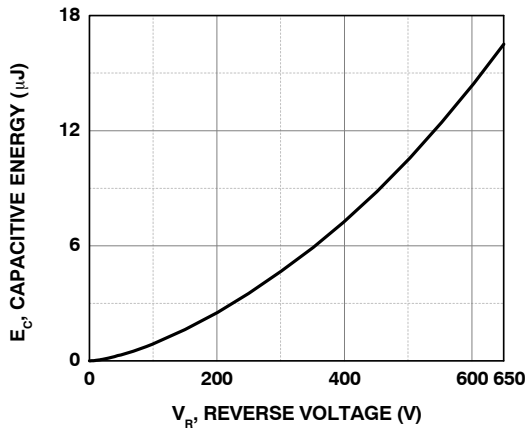


Figure 7. Capacitance Stored Energy

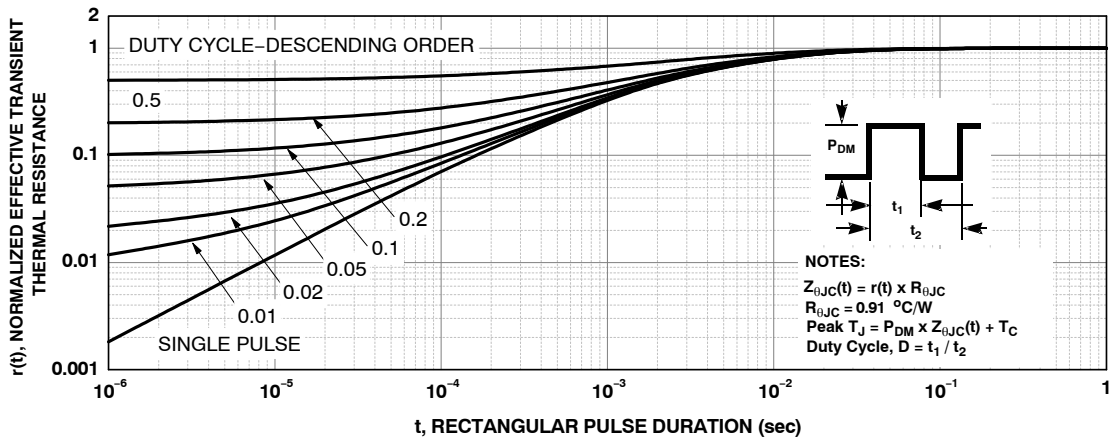


Figure 8. Junction-to-Case Transient Thermal Response Curve

# FFSH3065ADN-F155

## TYPICAL CHARACTERISTICS (T<sub>J</sub> = 25°C unless otherwise noted)

L = 0.5mH

R < 0.1Ω

V<sub>DD</sub> = 50V

EAVL = 1/2LI<sub>L</sub><sup>2</sup> [V<sub>R(AVL)</sub> / (V<sub>R(AVL)</sub> - V<sub>DD</sub>)]

Q1 = IGBT (BV<sub>CES</sub> > DUT V<sub>R(AVL)</sub>)

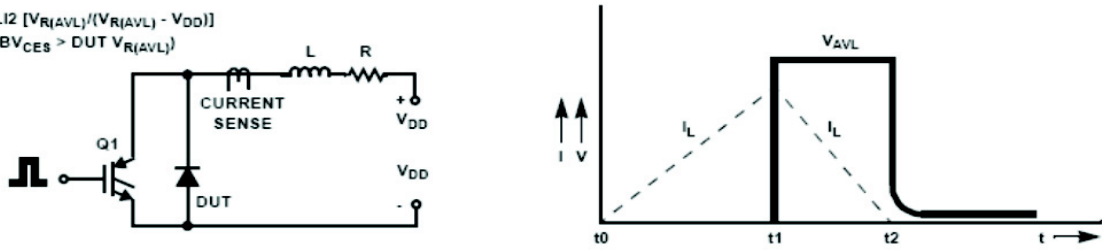


Figure 9. Unclamped Inductive Switching Test Circuit & Waveform

# MECHANICAL CASE OUTLINE

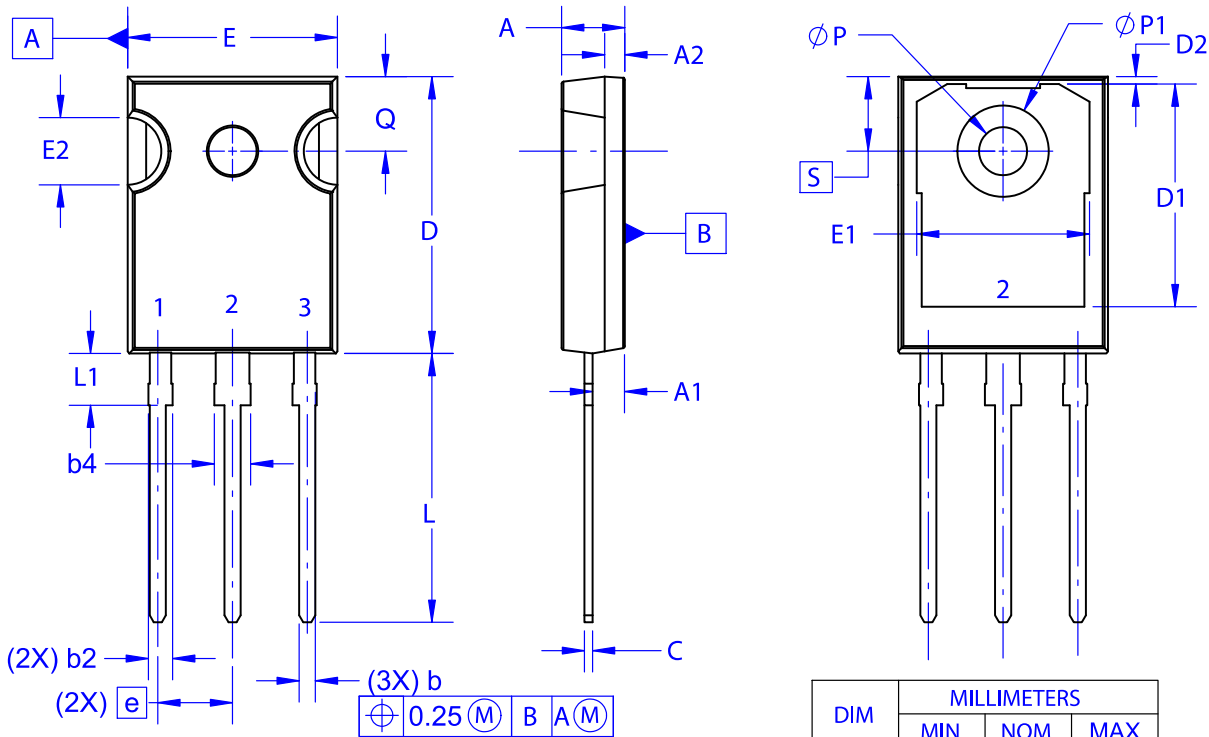
## PACKAGE DIMENSIONS

ON Semiconductor®



TO-247-3LD  
CASE 340CH  
ISSUE A

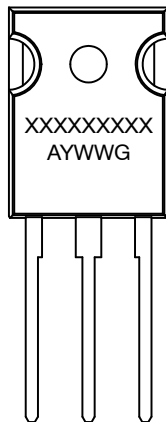
DATE 09 OCT 2019



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

### GENERIC MARKING DIAGRAM\*



XXXX = Specific Device Code  
A = Assembly Location  
Y = Year  
WW = Work Week  
G = Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

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<b>DESCRIPTION:</b>	<b>TO-247-3LD</b>	<b>PAGE 1 OF 1</b>

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